# MSKSEMI















**ESD** 

**TVS** 

**TSS** 

MOV

**GDT** 

**PLED** 

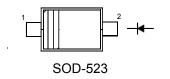
Broduct data speet





#### **Features**

- Fast switching speed
- Ultra-small surface mount package
- For general purpose switching applications
- High conductance



## **RNNING**

PIN DESCRIPTION Cathode Anode

MARK:T4

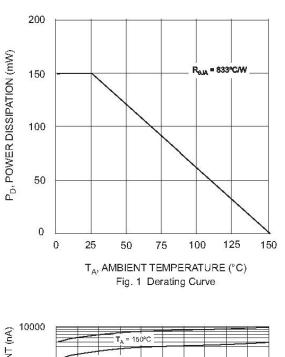
Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

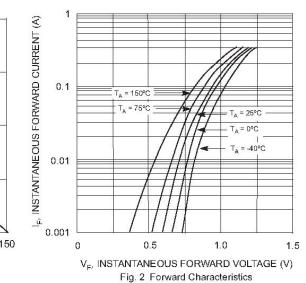
Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	100	V
Reverse Voltage	V <sub>R</sub>	75	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	125	mA
Forward Continuous Current	I <sub>FM</sub>	250	mA
Non-repetitive Peak Forward Surge Current at t = 1 µs at t = 100 m	s I <sub>FSM</sub>	2 1	Α
Power Dissipation	P <sub>tot</sub>	150	mW
Thermal Resistance Junction to Ambient Air	R <sub>èJA</sub>	833	°C/W
Operating Temperature Range	Tj	- 65 to + 150	°C
Storage Temperature Range	T <sub>stg</sub>	- 65 to + 150	°C

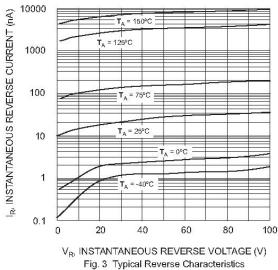
## Characteristics at T<sub>a</sub> = 25 °C

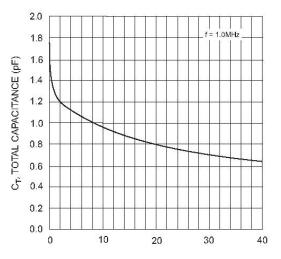
Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1 \mu A$	V <sub>(BR)R</sub>	75	-	٧
Forward Voltage at $I_F$ = 1 mA at $I_F$ = 10 mA at $I_F$ = 50 mA at $I_F$ = 150 mA	V <sub>F</sub>	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at $V_R$ = 75 V at $V_R$ = 20 V at $V_R$ = 75 V, $T_J$ = 150 °C at $V_R$ = 25 V, $T_J$ = 150 °C	I <sub>R</sub>		1 25 50 30	µА n А µА µА
Total Capacitance at V <sub>R</sub> = 0 V, f = 1 MHz	Ст	-	2	pF
Reverse Recovery Time at $I_{rr}$ = 0.1 X $I_R$ , $I_F$ = $I_R$ = 10 mA, $R_L$ = 100 $\Omega$	t <sub>rr</sub>	-	4	ns







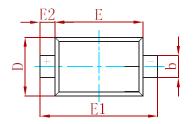


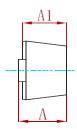


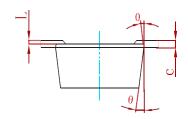
 $V_{R^{\prime}}$  REVERSE VOLTAGE (V) Fig. 4 Typical Capacitance vs. Reverse Voltage



## **PACKAGE MECHANICAL DATA**

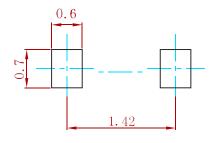






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	0.510	0.770	0.020	0.031	
A1	0.500	0.700	0.020	0.028	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	0.750	0.850	0.030	0.033	
E	1.100	1.300	0.043	0.051	
E1	1.500	1.700	0.059	0.067	
E2	0.200	REF	0.008	REF	
L	0.010	0.070	0.001	0.003	
0	7° F	REF	7° F	REF	

## **Suggested Pad Layout**



### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
1N4148WT-MS	SOD-523	3000



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